Supporting information

Complementary photo and temperature cured polymer dielectrics with high-quality dielectric properties for organic semiconductors

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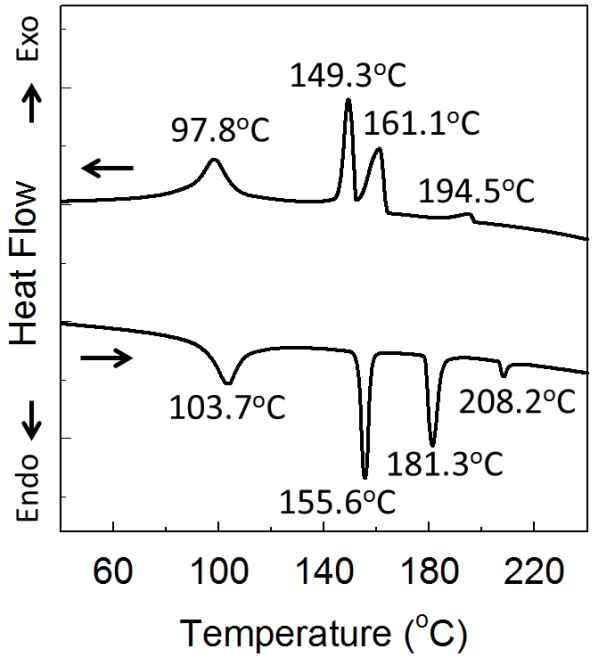

Fig. S1 Differential scanning calorimetry (DSC) heating and cooling curves of PTCDI-C13 powder with a scanning rate of 10 ^{o}C min^{-1}.

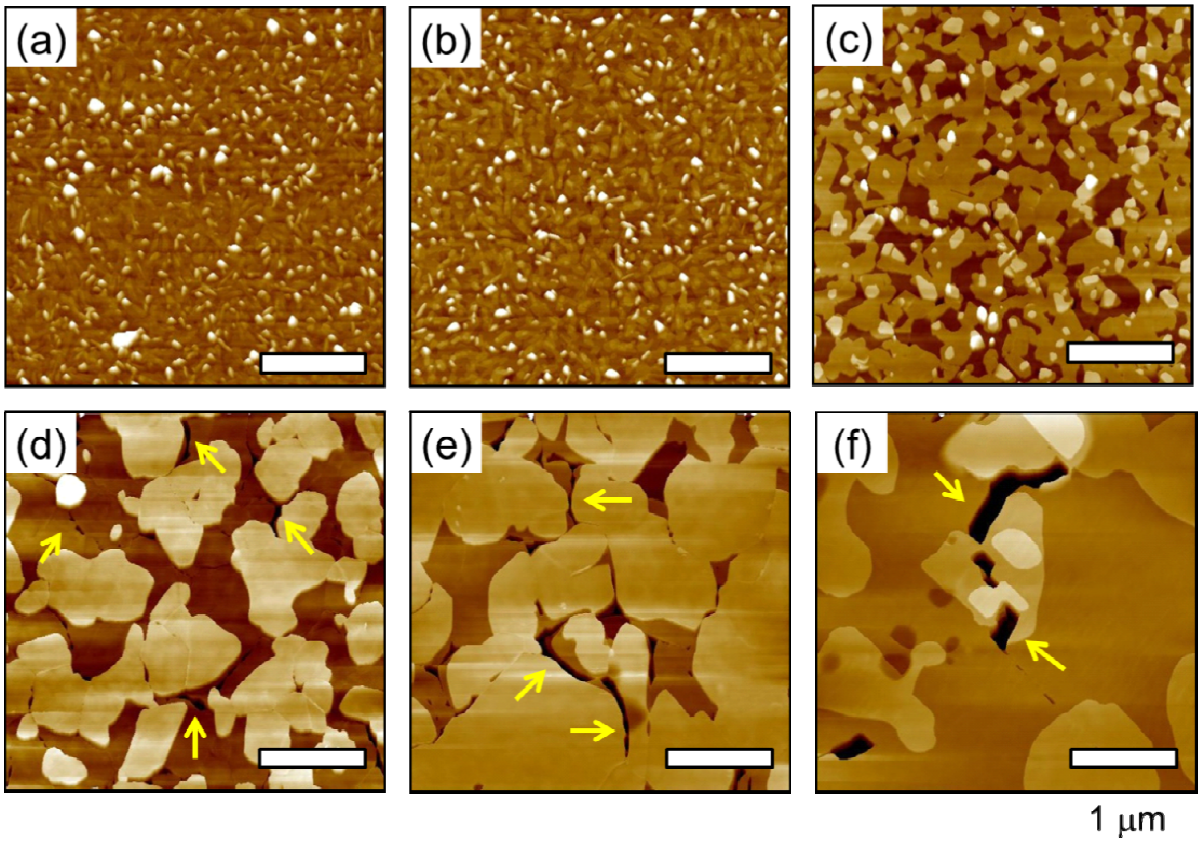

Fig. S2 AFM topographies of 50 nm thick PTCDI-C13 films on bare 300 nm thick SiO_2/Si substrates before and after thermally annealing at different T_As for 1 hr: (a) as-deposited, (b) 60 ^oC, (c) 100 ^oC, (d) 140 ^oC, (e) 160 ^oC, and (f) 200 ^oC, respectively. (Yellow arrowed marks in (d–f) indicate crystal grain boundaries of PTCDI-C13 films, due to the difference in thermal expansion coefficients between the film and substrate.)